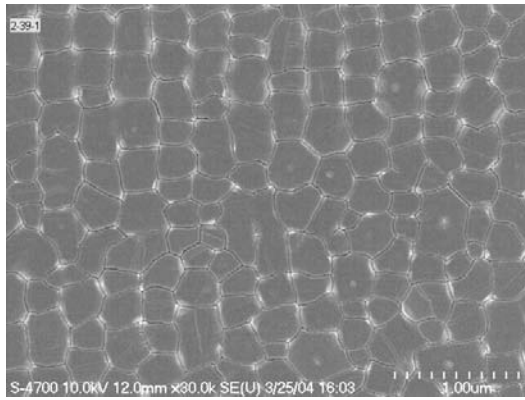
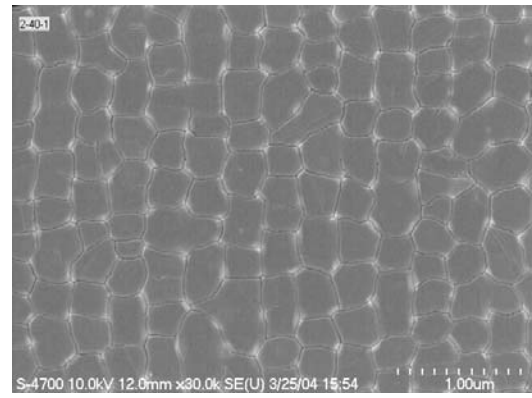


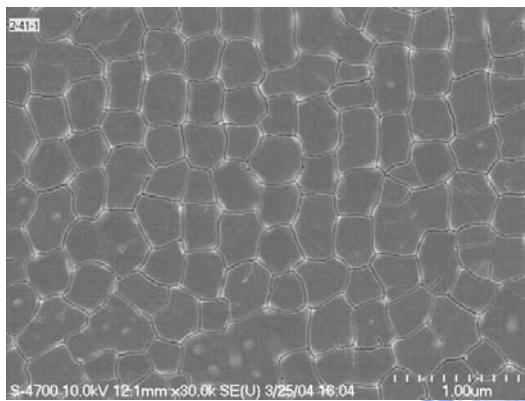
**Fig. 2-22** SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 330, (b) 340, (c) 350, (d) 360 (e) 370 (f) 380 mJ/cm<sup>2</sup>. The laser energy 950 mJ, frequency 300 Hz, power 285 W, scan speed 6 mm/sec, pitch 0.02 mm, beam width 0.4 mm, pre treatment clean with O3 20 ppm for 100 sec



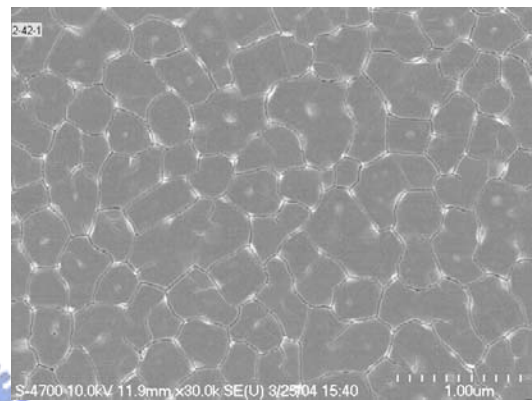
(a)



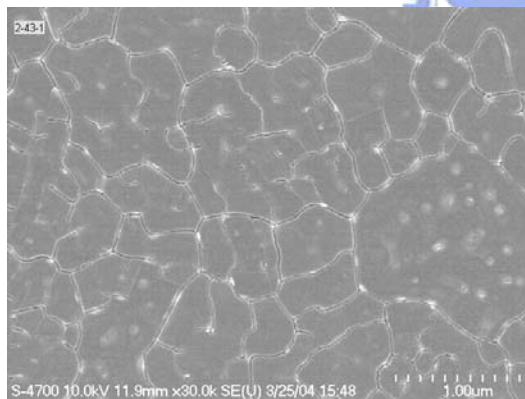
(d)



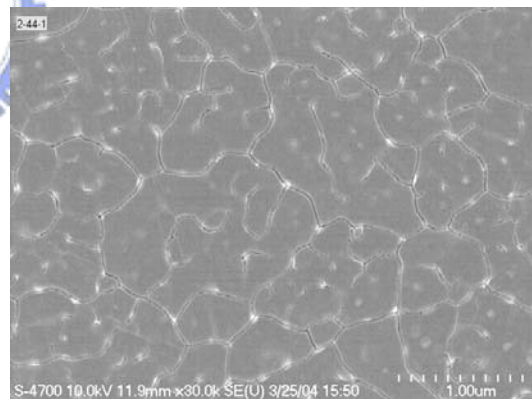
(b)



(e)



(c)



(f)

**Fig. 2-23** SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 390, (b) 400, (c) 410, (d) 420 (e) 430 (f) 440  $\text{mJ}/\text{cm}^2$ . The laser energy 950 mJ, frequency 300 Hz, power 285 W, scan speed 6 mm/sec, pitch 0.02 mm, beam width 0.4 mm, pre treatment clean with O3 20 ppm for 100 sec